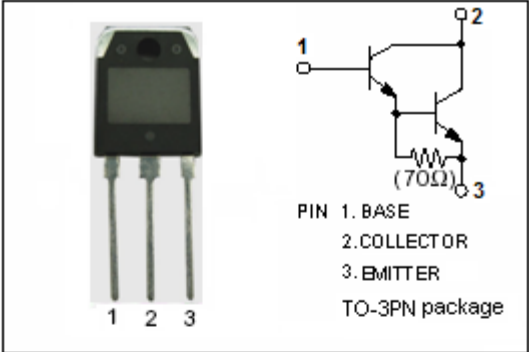


isc Silicon NPN Darlington Power Transistor

2SD2488

DESCRIPTION

- With TO-3PN package
- DARLINGTON
- High DC current gain

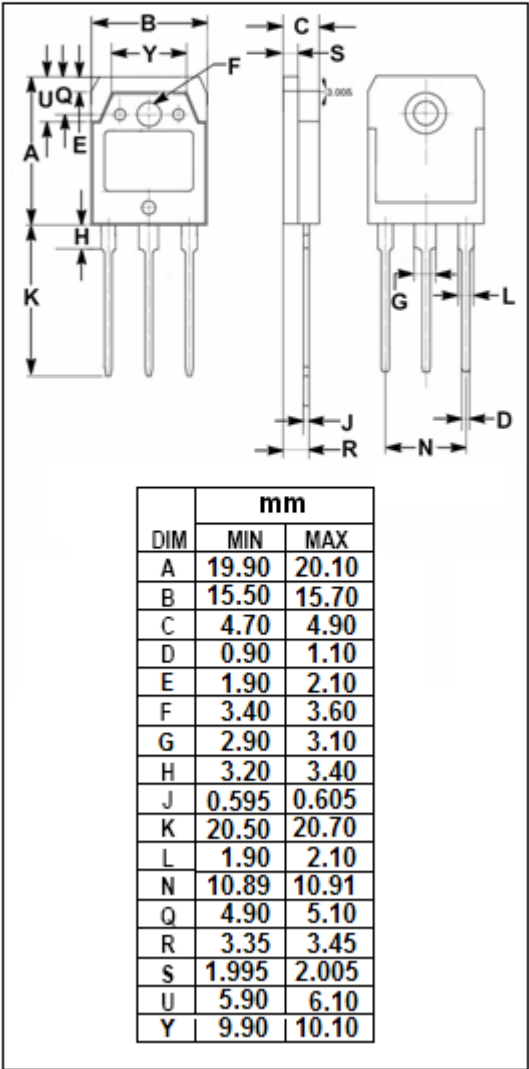


APPLICATIONS

- Audio ,regulator and general purpose

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYM BOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		15	A
I_B	Base current		1	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	130	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$



isc Silicon NPN Darlington Power Transistor**2SD2488****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =30mA ; I _B =0	200			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A ; I _B =10mA			2.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A ; I _B =10mA			3.0	V
I _{CBO}	Collector cut-off current	V _{CB} =200V I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =10A ; V _{CE} =4V	5000		30000	
C _{ob}	Output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		120		pF
f _T	Transition frequency	I _E =-2A ; V _{CE} =12V		70		MHz

◆ h_{FE} Classifications

O	P	Y
5000-12000	6500-20000	15000-30000